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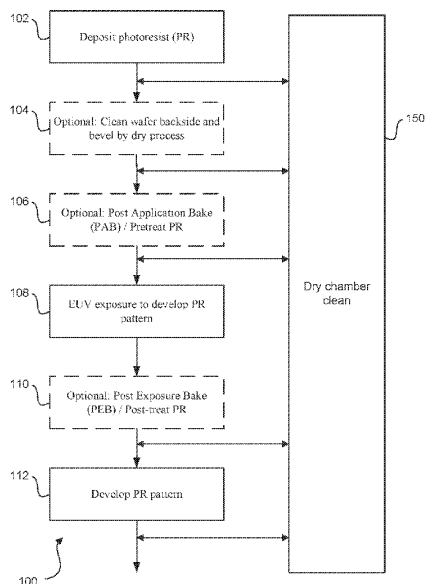


FIG. 1

(57) Abstract: Methods for making thin-films on semiconductor substrates, which may be patterned using EUV, include: depositing the organometallic polymer-like material onto the surface of the semiconductor substrate, exposing the surface to EUV to form a pattern, and developing the pattern for later transfer to underlying layers. The depositing operations may be performed by chemical vapor deposition (CVD), atomic layer deposition (ALD), and ALD with a CVD component, such as a discontinuous, ALD-like process in which metal precursors and counter-reactants are separated in either time or space.

SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN,
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